Vishay Semiconductors

胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787



Silicon NPN Phototransistor, RoHS Compliant



DESCRIPTION

BPW77 is a silicon NPN phototransistor with high radiant sensitivity in hermetically sealed TO-18 package with base terminal and glass lens. It is sensitive to visible and near infrared radiation.

FEATURES

· Package type: leaded Package form: TO-18

• Dimensions (in mm): Ø 4.7

· High photo sensitivity

· High radiant sensitivity

· Suitable for visible and near infrared radiation

Fast response times

• Angle of half sensitivity: $\varphi = \pm 10^{\circ}$

· Base terminal connected

· Hermetically sealed package

(Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

· Detector in electronic control and drive circuits

PRODUCT SUMMARY					
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.1} (nm)		
BPW77NA	7.5 to 15	± 10	450 to 1080		
BPW77NB	> 10	± 10	450 to 1080		

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
BPW77NA	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		
BPW77NB	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Collector base voltage	Y.C. TIM WY 100X	V _{CBO}	80	1700A.		
Collector emitter voltage	NY.COM TW	V _{CEO}	70	VY.		
Emitter base voltage	COM	V _{EBO}	5	V		
Collector current	00 r. ONI.I.	lc	50	mA mA		
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA		
Total power dissipation	T _{amb} ≤ 25 °C	P _V	250	mW		
Junction temperature	COMP.	Tron	125	°C		
Operating temperature range	M 100 1.	T _{amb}	- 40 to + 125	°C		
Storage temperature range	TOOY CO THE WAY	T _{stg}	- 40 to + 125	°C		
Soldering temperature	t ≤ 5 s	T _{sd}	260	°C		
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R _{thJA}	400	K/W		
Thermal resistance junction/gase	1100x.c M.T.	R _{thJC}	150	K/W		

T_{amb} = 25 °C, unless otherwise specified









Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors WWW.100Y.COM.T

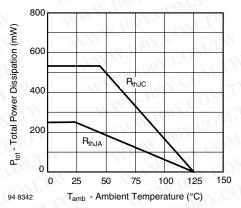


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70	107.C	TW	V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}	WWW	1CO	100	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}	Wire	6 0	M.	pF
Angle of half sensitivity	M. 1001.	φ	Maria	± 10	MIL	deg
Wavelength of peak sensitivity	WWW. OON.CO.	λ_{p}	MM	850	WILL	nm
Range of spectral bandwidth	TANN. 100 TI CON	λ _{0.1}	Wix	450 to 1080	Ohr.	nm
Collector emitter saturation voltage	E_e = 1 mW/cm ² , λ = 950 nm, I_C = 1 mA	V _{CEsat}	W	0.15	0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{on}	**	6	COM	μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t _{off}	4	5	COM.	μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f _c		110	T.	kHz

Note

T_{amb} = 25 °C, unless otherwise specified

Note T _{amb} = 25 °C, unless otherwise specified							
TYPE DEDICATED	CHARACTERISTICS	.1007.C	ONLIN		WWW.	ON CO	TY
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm},$	BPW77NA	Ica	7.5		15	mA
	$V_{CE} = 5 \text{ V}$	BPW77NB	I _{ca}	10	11.	11 100 J.	mA

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

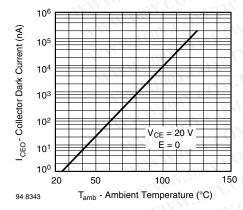


Fig. 2 - Collector Dark Current vs. Ambient Temperature

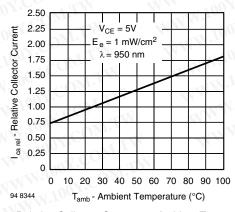


Fig. 3 - Relative Collector Current vs. Ambient Temperature

Vishay Semiconductors Silicon NPN Phototransistor, RoHS Compliant



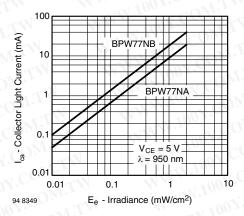


Fig. 4 - Collector Light Current vs. Irradiance

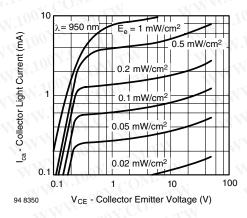


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

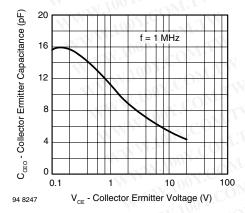


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

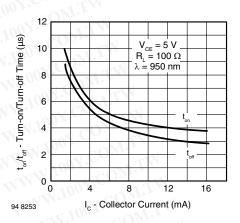


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

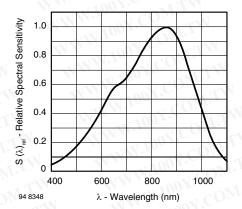


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

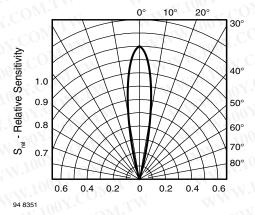
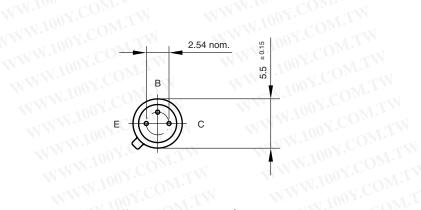


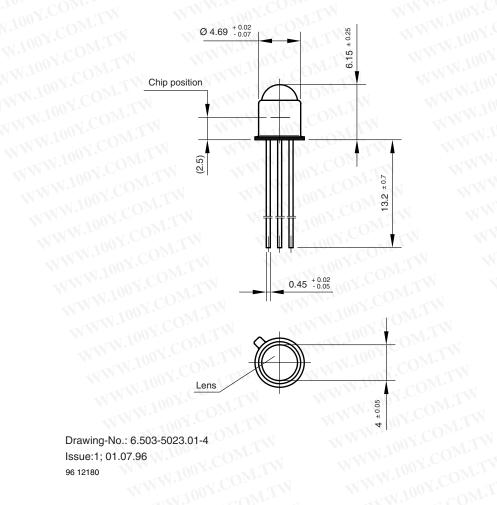
Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

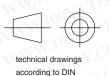


Silicon NPN Phototransistor, RoHS Compliant Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters







WWW.100Y.COM.TW

specifications

Drawing-No.: 6.503-5023.01-4

WWW.100Y.COM.TW Issue:1: 01.07.96

96 12180



特力材料886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishav or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

WWW.100Y.COM Document Number: 91000 www.vishay.com Revision: 11-Mar-11